
FOREWORD

Special Section on Fundamentals and Applications of Advanced Semiconductor Devices

The most important role of semiconductor devices and LSIs, at present and in future, is to contribute to “green society” through the improvement and development of their performances and new functionalities. The special section aims at discussing recent progress of semiconductor materials and devices in the entire field from fundamental physics to advanced device technologies. This section contains 34 papers including 3 invited papers.

I would like to express my sincere thanks to all the authors for their contributions to the special section. I also appreciate the editorial committee members and reviewers. Despite of the busy and tight schedule, they spent precious time to do hard work for editing and reviewing papers. Without their efforts, we could not get this invaluable special section.

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Tamotsu Hashizume, Guest Editor

Tamotsu Hashizume (*Member*) was born in Hokkaido in 1956. He received B.E. and Ph.D. degrees in electrical engineering from Hokkaido University, Hokkaido, Japan, in 1981 and 1991, respectively. He became Research Associate of Kushiro National College of Technology in 1981. In 1994, he moved to Hokkaido University, as Associate Professor. Since 2004, he has been a Professor of Research Center for Integrated Quantum Electronics, Hokkaido University. His research interests include characterization and control of surfaces and interfaces of GaN-based materials for electron device application. He has authored or co-authored over 150 papers in scientific and technical journals. From 2009 to 2011, he served as chair of the Electron Devices (ED) Technical Committee of IEICE.

